





## LOW $V_{CE(SAT)}$ PNP SURFACE MOUNT TRANSISTOR

## **Features**

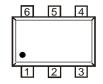
- Epitaxial Planar Die Construction
- Complementary NPN Type Available (DNLS160V)
- Surface Mount Package Suited for Automated Assembly
- Ultra Small Surface Mount Package
- Lead Free/RoHS Compliant (Note 1)
- "Green Device" (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability



SOT-563

## **Mechanical Data**

- Case: SOT-563
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.003 grams (approximate)





## **Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-80	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-60	V
Emitter-Base Voltage	V <sub>EBO</sub>	-5	V
Collector Current - Continuous	Ic	-1	Α
Peak Pulse Collector Current	I <sub>CM</sub>	-2	Α
Base Current (DC)	I <sub>B</sub>	-300	mA

## **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3) @ T <sub>A</sub> = 25°C	P <sub>D</sub>	300	mW
Thermal Resistance, Junction to Ambient (Note 3) @ T <sub>A</sub> = 25°C	$R_{ heta JA}$	417	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

Notes:

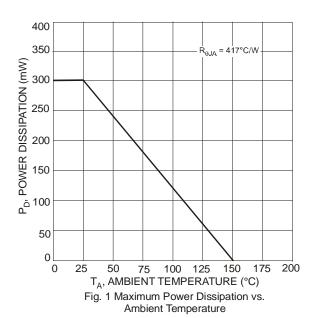
- 1. No purposefully added lead.
- 2. Diode's Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php.
- 3. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

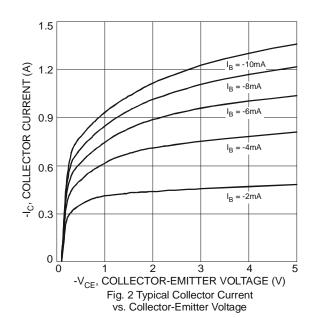


## **Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

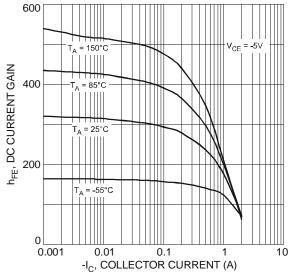
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 4)							
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-80	_	_	V	$I_C = -100 \mu A, I_E = 0$	
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	-60	_	_	V	$I_C = -10 \text{mA}, I_B = 0$	
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	<del>-</del> 5	_	_	V	$I_E = -100 \mu A, I_C = 0$	
Collector Cutoff Current	I <sub>CBO</sub>	-	_	-100	nA	$V_{CB} = -60V, I_{E} = 0$	
Collector Cutoff Current				-50	μΑ	$V_{CB} = -60V$ , $I_E = 0$ , $T_A = 150$ °C	
Collector Cutoff Current	I <sub>CES</sub>		_	-100	nA	$V_{CE} = -60V, V_{BE} = 0$	
Emitter Cutoff Current	I <sub>EBO</sub>		_	-100	nA	$V_{EB} = -5V, I_C = 0$	
ON CHARACTERISTICS (Note 4)							
		200	325	_		$V_{CE} = -5V$ , $I_C = -1mA$	
DC Current Gain	$h_{FE}$	150	250	_	V	$V_{CE} = -5V, I_{C} = -500mA$	
		100	180	_		$V_{CE} = -5V, I_{C} = -1A$	
		_	-90	-160		$I_C = -100 \text{mA}, I_B = -1 \text{mA}$	
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	_	-90	-175	mV	$I_C = -500 \text{mA}, I_B = -50 \text{mA}$	
		_	-160	-330		$I_C = -1A$ , $I_B = -100mA$	
Collector-Emitter Saturation Resistance	R <sub>CE(SAT)</sub>	_	160	330	mΩ	$I_C = -1A$ , $I_B = -100mA$	
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>		-0.95	-1.1	V	$I_C = -1A$ , $I_B = -50mA$	
Base-Emitter Turn On Voltage	V <sub>BE(ON)</sub>		-0.82	-0.9	V	$V_{CE} = -5V, I_{C} = -1A$	
SMALL SIGNAL CHARACTERISTICS							
Output Capacitance	C <sub>obo</sub>		10	15	pF	V <sub>CB</sub> = -10V, f = 1.0MHz	
Current Gain-Bandwidth Product	f⊤	150	220	_	MHz	$V_{CE} = -10V$ , $I_{C} = -50mA$ , $f = 100MHz$	
SWITCHING CHARACTERISTICS							
Turn-On Time	t <sub>on</sub>	_	36		ns		
Delay Time	t <sub>d</sub>	_	12	_	ns		
Rise Time	t <sub>r</sub>		24	_	ns	V <sub>CC</sub> = -10V	
Turn-Off Time	t <sub>off</sub>		163	_	ns	$I_C = -0.5A$ , $I_{B1} = I_{B2} = -25mA$	
Storage Time	ts		132	_	ns		
Fall Time	t <sub>f</sub>	_	31	_	ns		

Notes: 4. Measured under pulsed conditions. Pulse width =  $300\mu s$ . Duty cycle  $\leq 2\%$ .

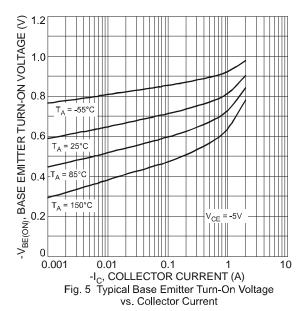








-I<sub>C</sub>, COLLECTOR CURRENT (A)
Fig. 3 Typical DC Current Gain vs. Collector Current



120 100 CAPACITANCE (pF) 80 20 0 0.01 100 V<sub>R</sub>, REVERSE VOLTAGE (V) Fig. 7 Typical Total Capacitance

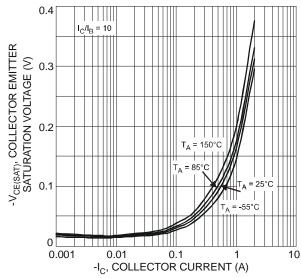


Fig. 4 Typical Collector Emitter Saturation Voltage vs. Collector Current

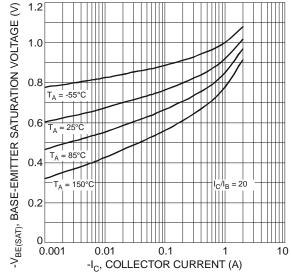
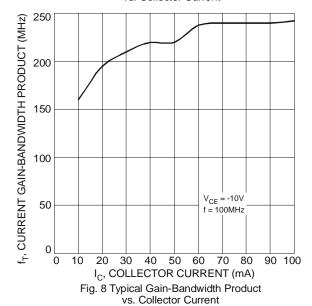


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current



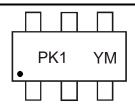


### Ordering Information (Note 5)

Device	Packaging	Shipping		
DPLS160V-7	SOT-563	3000/Tape & Reel		

Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

## **Marking Information**

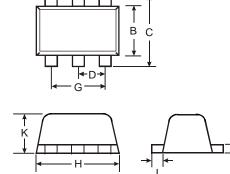


PK1 = Product Type Marking Code YM = Date Code Marking Y = Year ex: V = 2008 M = Month ex: 9 = September

#### Date Code Key

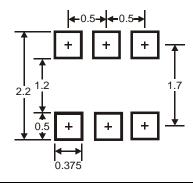
Year	2008		2009	2010		2011	2012		2013		2014		2015	i
Code	V		W	X		Υ	Z		Α		В		С	
Month	Jan	Feb	Mar	Apr	May	y Jun	Jul	Au	g Se	ep	Oct	No	v De	ес
Code	1	2	3	4	5	6	7	8	ę	a .	0	N	С	5

# **Package Outline Dimensions**



SOT-563							
Dim	Min	Max	Тур				
Α	0.15	0.30	0.20				
В	1.10	1.25	1.20				
O	1.55	1.70	1.60				
D	-	-	0.50				
Ð	0.90	1.10	1.00				
I	1.50	1.70	1.60				
K	0.55	0.60	0.60				
Г	0.10	0.30	0.20				
M	0.10	0.18	0.11				
All Dimensions in mm							

# Suggested Pad Layout (in mm)



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